

Electronic Supplementary Information

Aqueous phase preparation of ultrasmall MoSe₂ nanodots for efficient photothermal therapy of cancer cells

Lihui Yuwen,^a Jiajia Zhou,^a Yuqian Zhang,^a Qi Zhang,^a Jingyang Shan,^a Zhimin Luo,^a
Lixing Weng,^b Zhaogang Teng,^c and Lianhui Wang^{*,a}

a. Key Laboratory for Organic Electronics and Information Displays & Institute of Advanced Materials (IAM), Jiangsu National Synergetic Innovation Centre for Advanced Materials (SICAM), Nanjing University of Posts & Telecommunications, 9 Wenyuan Road, Nanjing 210023, China.

b. School of Geography and Biological Information, Nanjing University of Posts & Telecommunications, Nanjing 210023, China.

c. Department of Medical Imaging, Jinling Hospital, Clinical School of Medical College, Nanjing University, Nanjing 210002, China.

** Authors to whom correspondence should be addressed;*

Tel.: +86 25 85866333; Fax: +86 25 85866396.

E-mail: iamlhwang@njupt.edu.cn

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S1. Characterization of MoSe₂ NDs

TEM measurements were performed on a HT7700 electron microscopy (Hitachi, Japan) at an acceleration voltage of 100 kV. Field emission transmission electron microscopy JEM-2100F (JEOL, 200 kV) was used to obtain high-resolution TEM images. Energy-dispersive X-ray spectroscopy (EDS) data of MoSe₂ NDs was obtained from field-emission high-resolution scanning electron microscopy (S-4800, Hitachi) equipped with an energy-dispersive X-ray analyzer (EDAX). The UV-Vis-NIR absorption spectra of MoSe₂ NDs were recorded on an UV-3600 spectrophotometer (Shimadzu, Japan). Atomic force microscopy (AFM) images were acquired on Nanoscope IIIa (Bruker, USA). X-ray photoelectron spectroscopy (XPS) was performed using a PHI 5000 VersaProbe (Ulvac-Phi, Japan) with Al K α ($h\nu=1486.6$ eV) as the excitation source. X-ray diffraction patterns were obtained by using a D8 ADVANCE X-ray diffractometer (Bruker, Germany) with Cu K α radiation. Raman spectra were recorded on a micro-Raman spectroscopy system (Renishaw, UK) equipped with a 532 nm laser. The concentration of MoSe₂ NDs was determined by Inductively Coupled Plasma Optical Emission Spectrometer (ICP-OES, Optima 5300DV, Perkin Elmer). Photothermal study was performed by using a 785 nm continuous-wave semiconductor laser as light source (BWT Beijing, China). The temperature of the samples was detected by a non-contact visual IR thermometer (Fluke VT02). The power density of laser irradiation was measured by a digital power meter (PM100D, Thorlabs, USA). DLS and Zeta potential were performed on a ZetaPALS Potential Analyzer (Brookhaven Instruments Corporation, USA).

S2. The size distribution and Zeta potential of MoSe₂ NDs

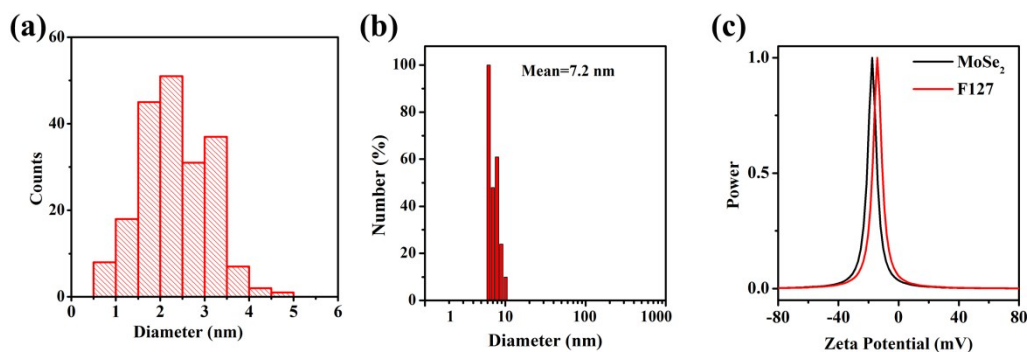


Fig. S1 (a) Size statistics of MoSe₂ NDs based on more than 150 nanoparticles by TEM; (b) Hydrodynamic size and (c) Zeta potential of MoSe₂ NDs determined by DLS.

S3. EDS of MoSe₂ NDs

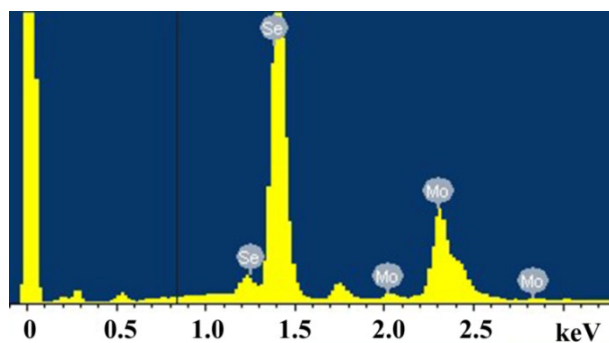


Fig. S2 Energy-dispersive X-ray spectroscopy (EDS) of MoSe₂ NDs.

S4. Calculation of Extinction coefficient

According to the Beer-Lambert Law (Eq. 1), the mass extinction coefficient ε of the MoSe₂ NDs can be calculated using Eq. 2:

$$A = \varepsilon LC \quad (1)$$

$$\varepsilon = \frac{A}{LC} \quad (2)$$

The term A refers to the absorbance of MoSe₂ NDs at 785 nm, ε is the mass extinction coefficient of MoSe₂ NDs (Lg⁻¹cm⁻¹), L is the optical length of the quartz cuvette (cm), and C is the mass concentration (gL⁻¹).

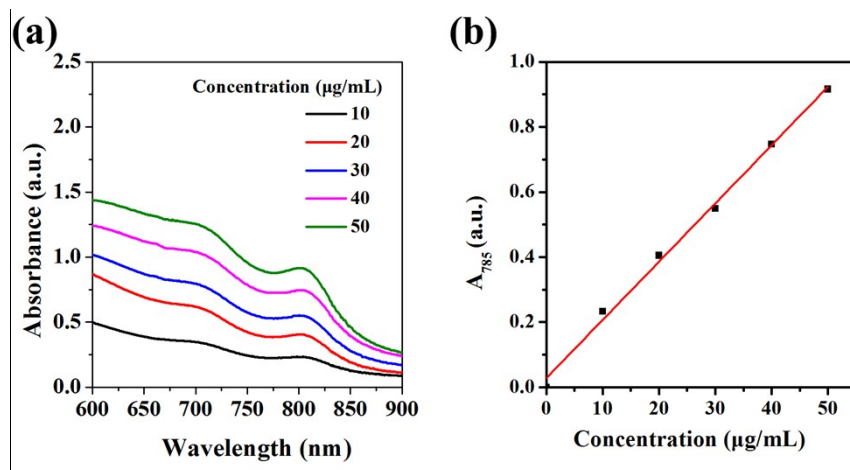


Fig. S3 (a) UV-vis-NIR absorption spectra of MoSe₂ NDs aqueous dispersion with different concentrations (10, 20, 30, 40, and 50 µg/ml); (b) The linearly fitted plots of absorbance versus concentration of MoSe₂ NDs aqueous suspension at 785 nm.

S5. Calculation of Photothermal Conversion Efficiency

Under laser irradiation at 785 nm, the temperature of MoSe₂ NDs aqueous suspensions increases dT in a short time dt, the total energy change can be expressed using Eq.3, as follows:

$$\sum_i m_i C_{p,i} \frac{dT}{dt} = Q_{ND} + Q_0 - Q_e \quad (3)$$

Where m_i and C_{p,i} are the mass and specific heat capacity of component i, Q_{ND} is the heat input of the absorbed laser energy by MoSe₂ NDs, Q₀ is the energy absorbed by the sample vial and solvent, and Q_e is the sum of heat dissipated to the surrounding environment by conduction, radiation, and so on.

$$Q_{ND} = I_0(1-10^{-A})\eta \quad (4)$$

The energy input from MoSe₂ NDs can be calculated from Eq. 4, where I₀ refers to the incident power of laser irradiation, A is the absorbance of the MoSe₂ NDs suspension, and η is the photothermal conversion efficiency of MoSe₂ NDs at 785 nm.

$$Q_e = hS(T - T_s) \quad (5)$$

The total external heat flux of the system presents in Eq. 5, where h is the heat transfer coefficient, S is the surface area of the sample vial, and T_s is the temperature of surrounding environment.

$$\theta \equiv \frac{T - T_s}{T_{\max} - T_s} \quad (6)$$

In order to describe a dimensional driving force temperature, θ is defined in Eq. 6, where T_{max} is the steady-state temperature of the system, T is the transient temperature of the system. A thermal equilibrium system time constant τ_s is defined as Eq. 7.

$$\tau_s \equiv \sum_i m_i C_{p,i} / hS \quad (7)$$

From all the equations mentioned above, dθ/dt can be expressed in the form of Eq. 8.

$$\frac{d\theta}{dt} = \frac{1}{\tau_s} \left[\frac{Q_{ND} + Q_0}{hS(T_{\max} - T_s)} - \theta \right] \quad (8)$$

When the sample system under laser irradiation reaches the equilibrium temperature, the laser is turned off, and the system input energy Q_{ND}+Q₀=0. Thus, Eq. 8 can be changed to the following expression:

$$\frac{d\theta}{dt} = -\frac{\theta}{\tau_s} \quad (9)$$

At the initial moment of laser-off, the transient temperature of the system $T=T_{\max}$, and $\theta=1$ at $t=0$, which gives θ as:

$$\theta = \exp\left(-\frac{t}{\tau_s}\right) \quad (10)$$

Eq. 10 can be further rearranged to Eq. 11 by substituted Eq. 6 into the expression. By using Eq. 11, τ_s can be calculated to be 139.1 s by plotting t versus $\ln\theta$.

$$\ln\left(\frac{T - T_s}{T_{\max} - T_s}\right) = -\frac{1}{\tau_s}t \quad (11)$$

The heat transfer constant of the system hS can be determined to be 6.0 mW/°C by using Eq. 12, where $m=0.2$ g, $C=4.2$ J/g·°C, and $\tau_s = 139.1$ s.

$$hS = \frac{\sum_i m_i C_{p,i}}{\tau_s} \quad (12)$$

During the irradiating of laser, the total energy input is $Q_{ND}+Q_0$, and the system temperature increases until reaching the equilibrium temperature $T_{\max}$, at when the energy input equals heat transfer to surrounding environment, which can be described in Eq. 13.

$$Q_{ND} + Q_0 = hS(T_{\max} - T_s) \quad (13)$$

By substituting Eq. 4 and Eq. 5 into Eq. 13, the photothermal conversion coefficient η can be expressed in Eq. 14. Since hA has been calculated from Eq. 12, Q_0 is measured to be 54 mW, and other parameters in this system are as follows: $T_{\max}=50.4^\circ\text{C}$, $T_s=29.5^\circ\text{C}$, $A=0.0444$, $I_0=1600$ mW. The photothermal conversion coefficient (η) of MoSe₂ NDs is calculated to be 46.5%.

$$\eta = \frac{hS(T_{\max} - T_s) - Q_0}{I_0(1 - 10^{-A})} \quad (14)$$